

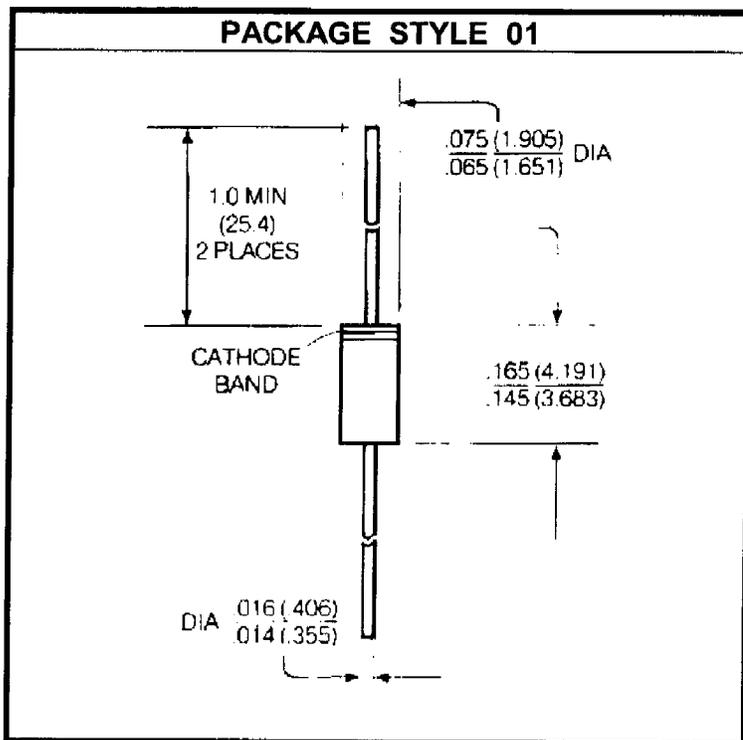
1N5719

DESCRIPTION:

The **1N5719** is a Silicon PIN Diode Designed for General Purpose Attenuator and Switching Applications from 100 MHz to 3 GHz.

MAXIMUM RATINGS

I_F	100 mA
V_R	150 V
P_{DISS}	250 mW @ $T_A = 25^\circ\text{C}$
T_J	-65°C to $+200^\circ\text{C}$
T_{STG}	-65°C to $+200^\circ\text{C}$
θ_{JC}	0.7°C/mW



CHARACTERISTICS $T_C = 25^\circ\text{C}$

SYMBOL	TEST CONDITIONS	MINIMUM	TYPICAL	MAXIMUM	UNITS
V_{BR}	$I_R = 10 \mu\text{A}$	150			V
C_T	$V_R = 100 \text{ V}$ $f = 1.0 \text{ MHz}$			0.3	pF
R_S	$I_F = 100 \text{ mA}$ $f = 100 \text{ MHz}$			1.25	Ω
τ	$I_F = 50 \text{ mA}$ $I_R = 250 \text{ mA}$	100			μS
t_{rr}	$V_R = 10 \text{ V}$ $f = 20 \text{ mA}$		100		μS



NJ Semi-Conductors reserves the right to change test conditions, parameter limits and package dimensions without notice. Information furnished by NJ Semi-Conductors is believed to be both accurate and reliable at the time of going to press. However NJ Semi-Conductors assumes no responsibility for any errors or omissions discovered in its use. NJ Semi-Conductors encourages customers to verify that datasheets are current before placing orders.